

Supporting Information for:

Blocking recombination centers by controlling the charge density of sulfur vacancy in antimony trisulfide

Xiao Han, Qi Zhao, Xiaodan, Yan, Ting Meng*, Jinlu He*

College of Chemistry and Chemical Engineering, Inner Mongolia University, Hohhot

010021, PR China

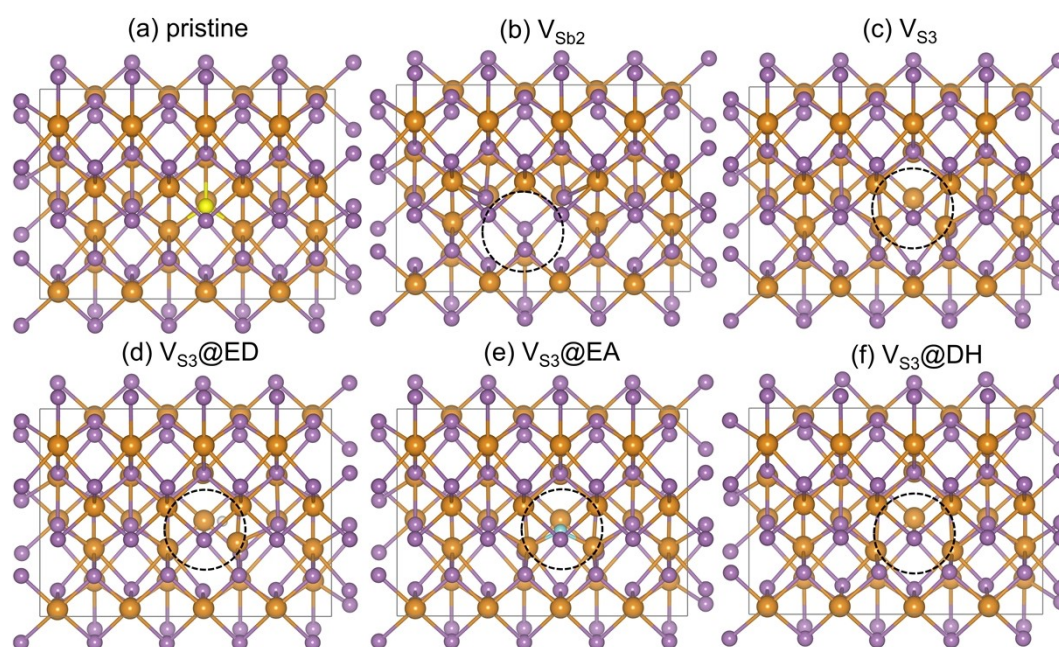


Fig. S1 Side views of optimized geometries for (a) pristine Sb_2S_3 , (b) $V_{\text{Sb}2}$, (c) $V_{\text{S}3}$, (d) $V_{\text{S}3}@ED$, (e) $V_{\text{S}3}@EA$ and (f) $V_{\text{S}3}@DH$ systems. The Sb, S, O and H atoms are colored in orange, purple, light blue and white, respectively. The removed sulfur atom is colored in yellow for pristine Sb_2S_3 system. The dotted line circle denote the defect and elements doping region.

* Corresponding author, E-mail: t.meng@imu.edu.cn; hejinlu@imu.edu.cn.

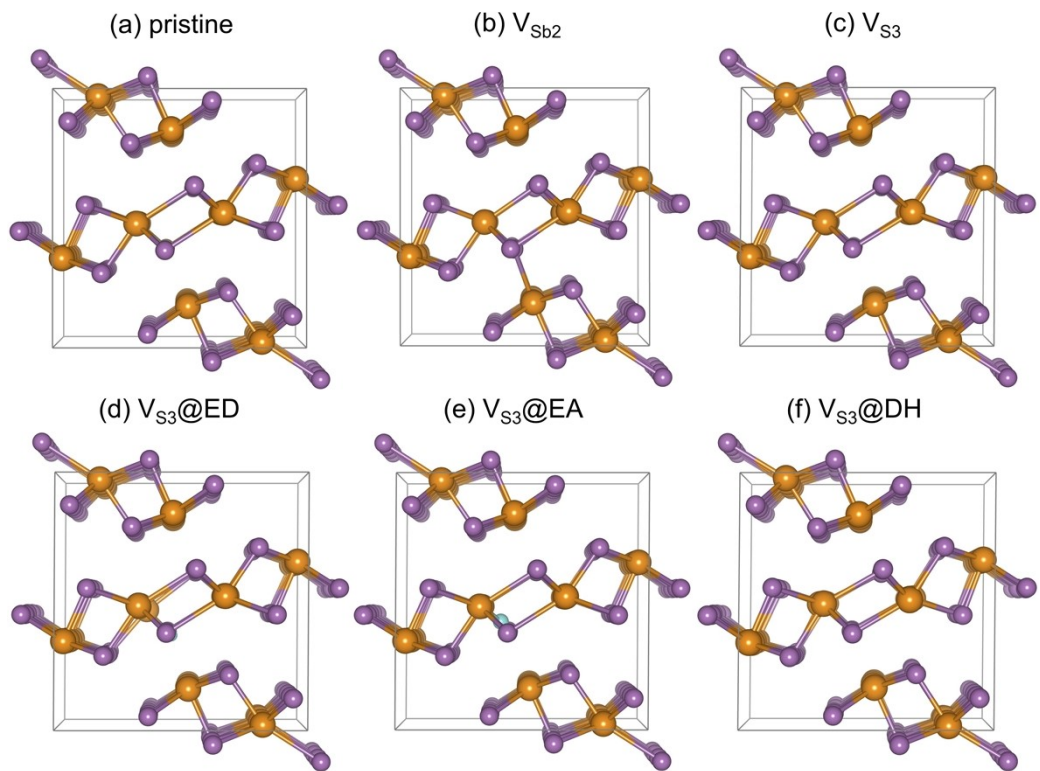


Fig. S2 Top views of optimized geometries for (a) pristine Sb_2S_3 , (b) V_{Sb_2} , (c) V_{S_3} , (d) $V_{\text{S}_3@\text{ED}}$, (e) $V_{\text{S}_3@\text{EA}}$ and (f) $V_{\text{S}_3@\text{DH}}$ systems. The Sb, S, O, and H atoms are colored in orange, purple, light blue and white, respectively. The removed sulfur atom is colored in yellow for pristine Sb_2S_3 system.

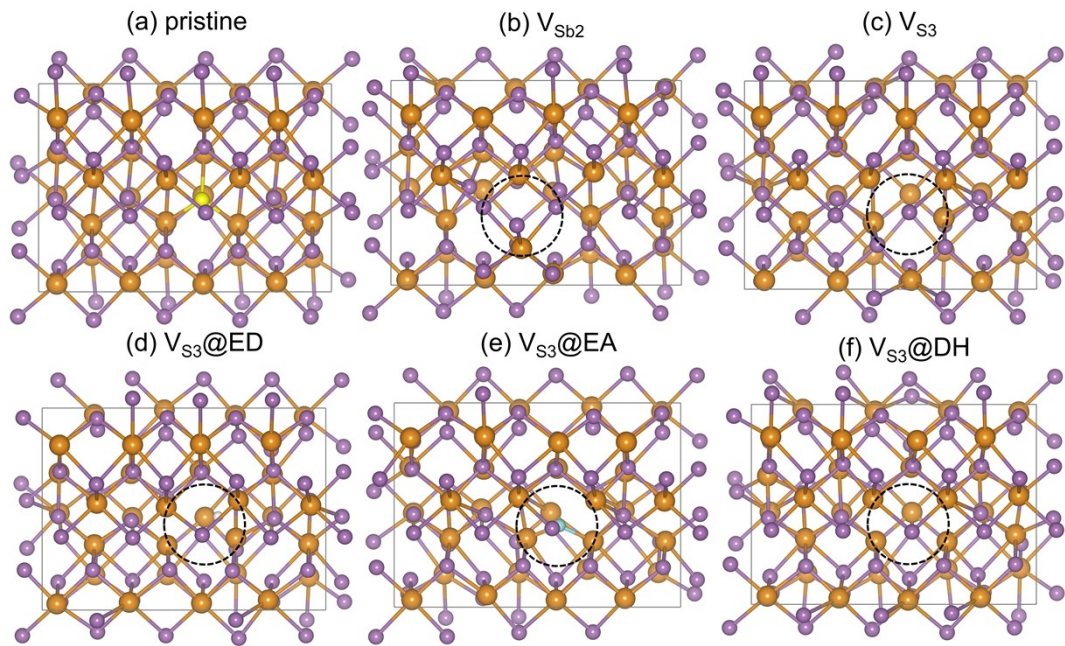


Fig. S3 Side views of representative geometries of 4 ps MD trajectories for (a) pristine Sb_2S_3 , (b) V_{Sb_2} , (c) V_{S_3} , (d) $V_{\text{S}_3}@ED$, (e) $V_{\text{S}_3}@EA$ and (f) $V_{\text{S}_3}@DH$ systems at 300 K. The Sb, S, O, and H atoms are colored in orange, purple, light blue and white, respectively. The removed sulfur atom is colored in yellow for pristine Sb_2S_3 system.

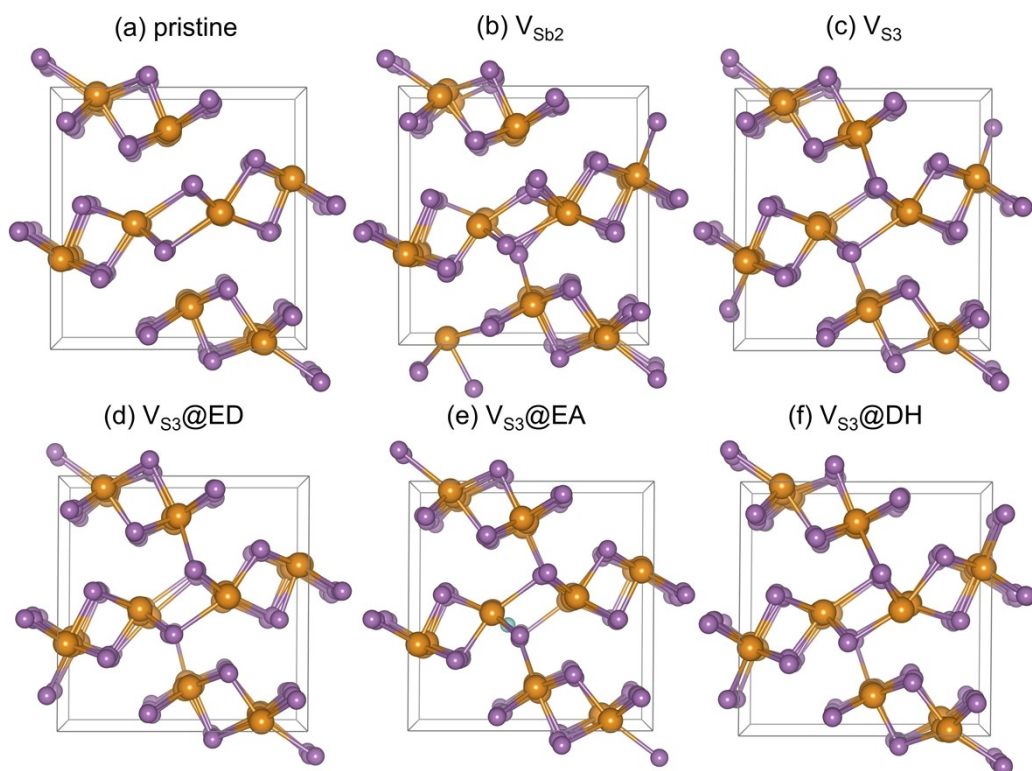


Fig. S4 Top views of representative geometries of 4 ps MD trajectories for pristine Sb_2S_3 , $V_{\text{Sb}2}$, $V_{\text{S}3}$, $V_{\text{S}3@\text{ED}}$, $V_{\text{S}3@\text{EA}}$ and $V_{\text{S}3@\text{DH}}$ systems at 300 K. The Sb, S, O, and H atoms are colored in orange, purple, light blue and white, respectively. The removed sulfur atom is colored in yellow for pristine Sb_2S_3 system.

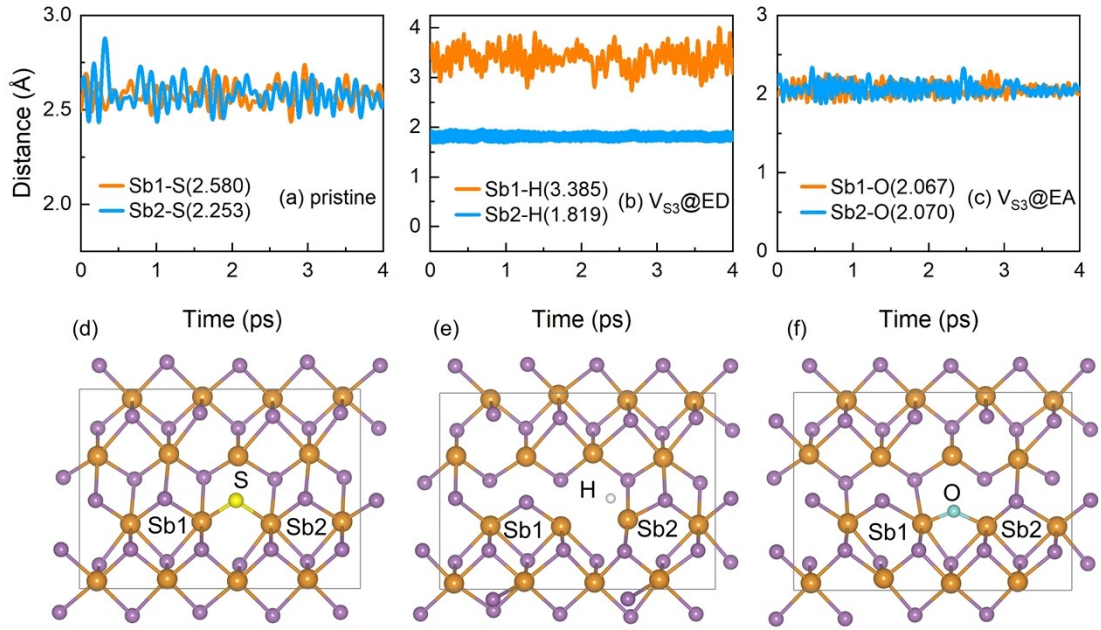


Fig. S5. Top panel shows evolution of the Sb-M (M = S, H and O) distances for pristine (a) Sb_2S_3 , (b) $V_{S_3}@ED$ and (c) $V_{S_3}@EA$ systems. The bottom panel shows geometries for pristine (a) Sb_2S_3 , (b) $V_{S_3}@ED$ and (c) $V_{S_3}@EA$ system. The numbers inside the parentheses are canonically averaged distance of Sb-M bonds. The Sb, S, O, and H atoms are colored in orange, purple, light blue and white, respectively. The removed sulfur atom is colored in yellow for pristine Sb_2S_3 system.

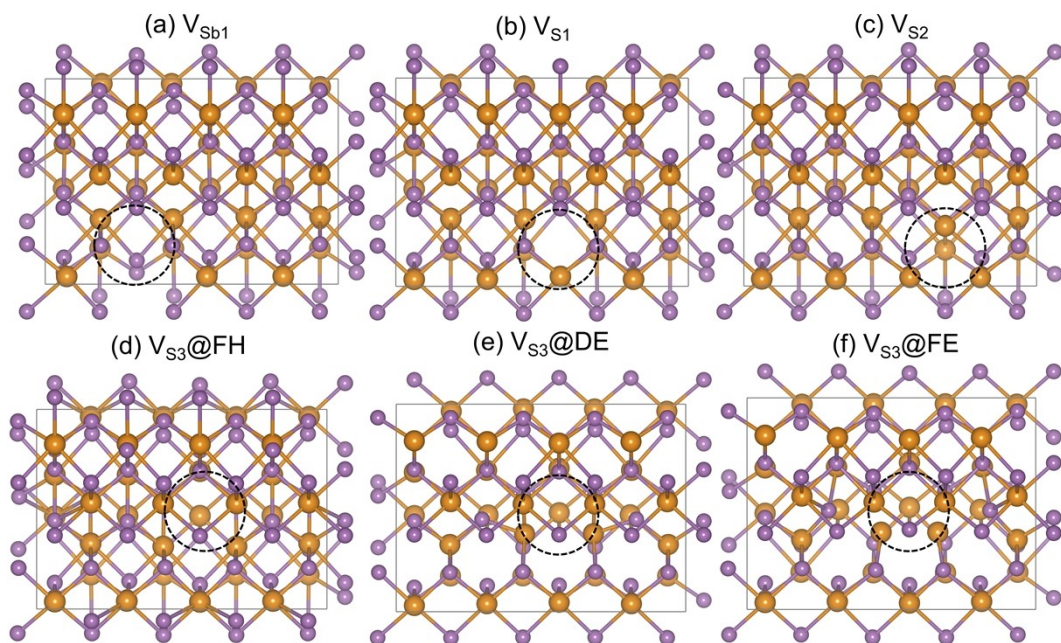


Fig. S6 Side views of optimized geometries for V_{Sb1} , V_{S1} , V_{S2} , $V_{S3@FH}$, $V_{S3@DE}$ and $V_{S3@FE}$ systems. The Sb and S atoms are colored in orange and purple, respectively.

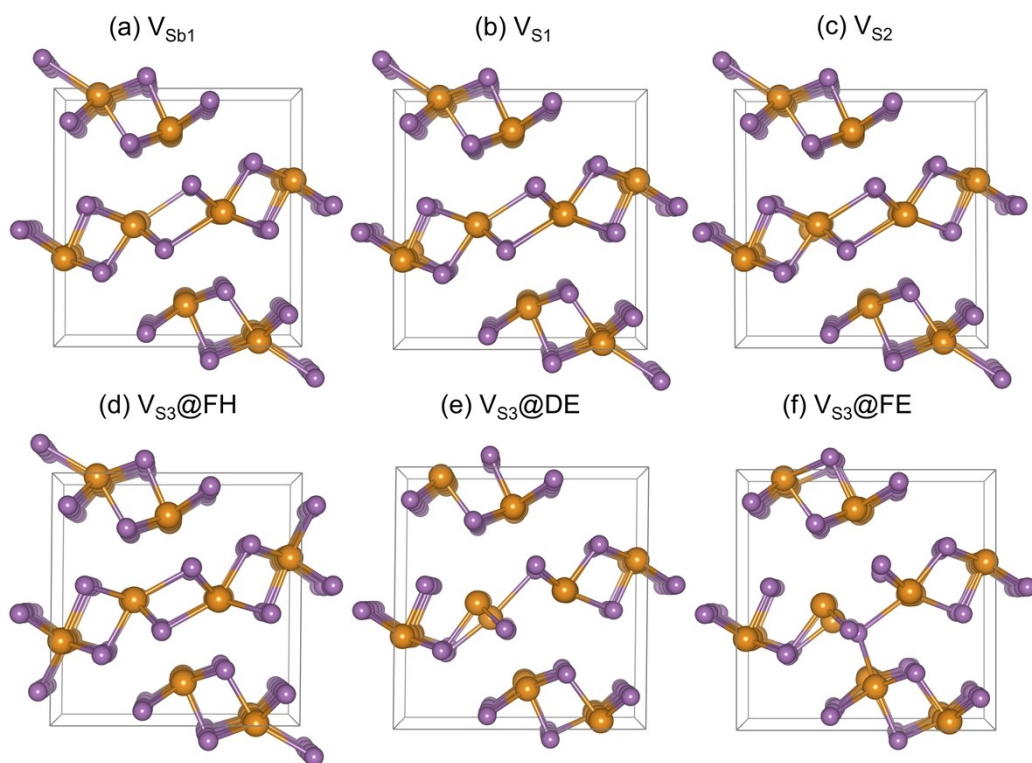


Fig. S7 Top views of optimized geometries for V_{Sb1} , V_{S1} , V_{S2} , $V_{S3@FH}$, $V_{S3@DE}$ and $V_{S3@FE}$ systems. The Sb and S atoms are colored in orange and purple, respectively.

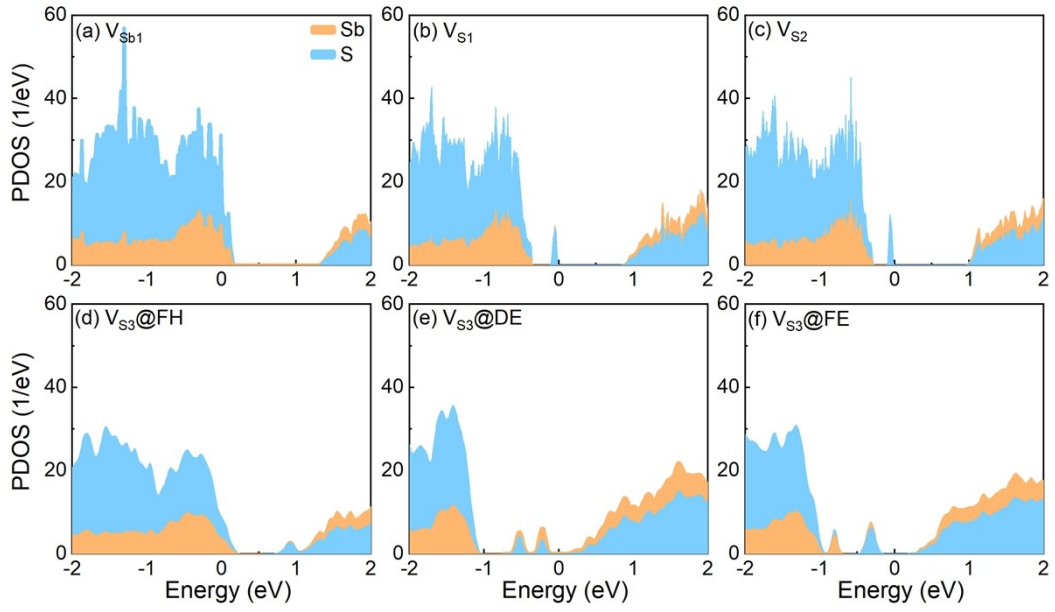


Fig. S8. Projected density of states (PDOS) of (a) V_{Sb1} , (b) V_{S1} , (c) V_{S2} , (d) $V_{S3@FH}$, (e) $V_{S3@DE}$ and (f) $V_{S3@FE}$ systems calculated using the PBE functional. Zero energy is set to the Fermi level.

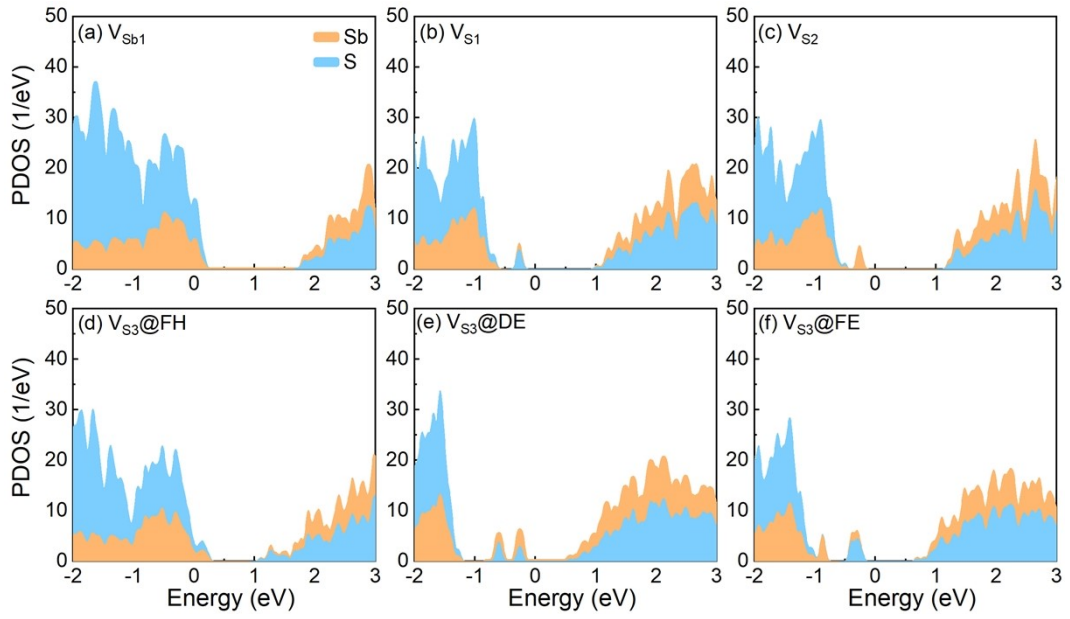


Fig. S9. Projected density of states (PDOS) of (a) V_{Sb1} , (b) V_{S1} , (c) V_{S2} , (d) $V_{S3@FH}$, (e) $V_{S3@DE}$ and (f) $V_{S3@FE}$ systems calculated using the HSE06 functional. Zero energy is set to the Fermi level.

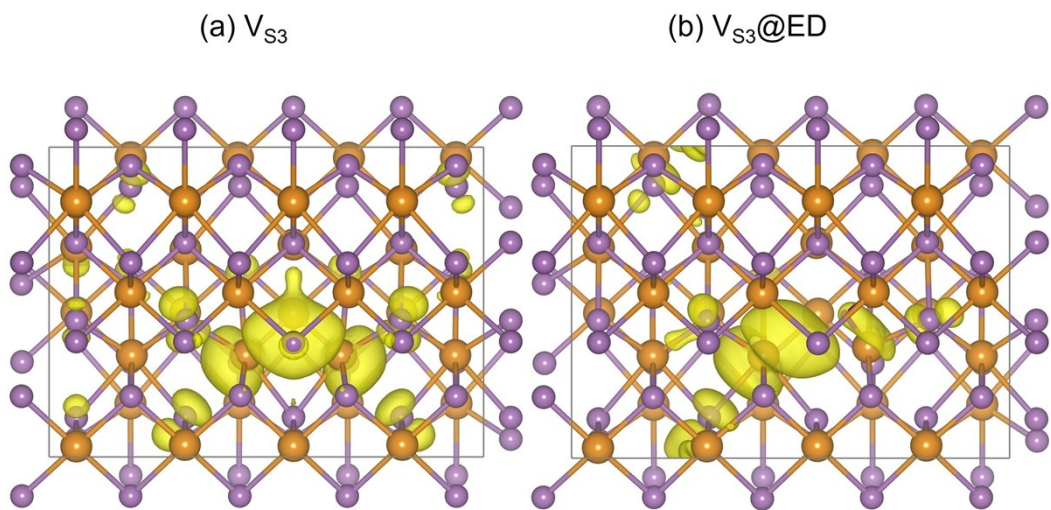


Fig. S10. Charge densities of the high charge density trap state in (a) V_{S3} , and (b) $V_{S3}@ED$ systems.

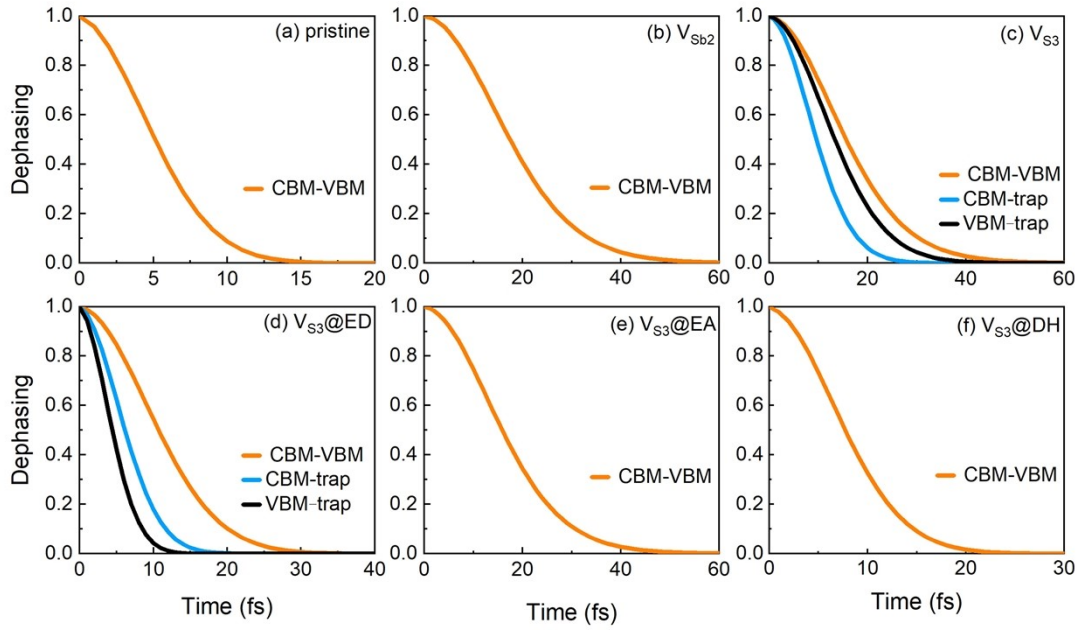


Fig. S11. Pure-dephasing functions for the key pairs of states for charge trapping and recombination in (a) pristine Sb_2S_3 , (b) V_{Sb_2} , (c) V_{S_3} , (d) $V_{\text{S}_3@ED}$, (e) $V_{\text{S}_3@EA}$ and (f) $V_{\text{S}_3@DH}$ systems.